

Docket No. 741756-2653
Application No. 0/688,969
Page 2

IN THE CLAIMS:

1-2. (Canceled)

3. (Currently Amended) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film; and
a hard mask formed over the gate electrode; and
an interlayer insulating film over the hard mask,
wherein the interlayer insulating film is in contact with at least a part of a lateral face
of the gate electrode.

4. (Currently Amended) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film;
a hard mask formed over the gate electrode; and
an interlayer insulating film over the hard mask; and
a conductive film which is in contact with the gate electrode,
wherein the interlayer insulating film is in contact with at least a part of a lateral face
of the gate electrode, and
wherein the conductive film is to serve as a wire for sending a signal to the gate
electrode or as a connection layer for connecting a wire with the gate electrode.

5-8. (Canceled)

9. (Original) A semiconductor device, according to claim 3, wherein the gate
electrode is selected from the group consisting of tantalum nitride and tungsten.

10. (Original) A semiconductor device, according to claim 3, wherein the hard mask
is selected from the group consisting of silicon oxide.

11. (Original) A semiconductor device, according to claim 4, wherein the gate
electrode is selected from the group consisting of tantalum nitride and tungsten.

W633697.1

Best Available Copy

Docket No. 740756-2653
Application No. 0/688,969
Page 3

12. (Original) A semiconductor device, according to claim 4, wherein the hard mask is selected from the group consisting of silicon oxide.

13. (Original) A semiconductor device, according to claim 4, wherein the conductive film is selected from the group consisting of tantalum nitride and tungsten.

14. (Previously Presented) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film; and,
an island shaped hard mask formed over the gate electrode,
wherein side walls of the island shaped hard mask have an angle of inclination of 0° or more, and of 90° or less.

15. (Previously Presented) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film; and,
an island shaped hard mask formed over the gate electrode,
wherein side walls of the island shaped hard mask forms arc shapes.

16. (Previously Presented) A semiconductor device, according to claim 14, wherein the angle is inclination of 35° or more, and 50° or less.

17. (Previously Presented) A semiconductor device, according to claim 14, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

18. (Previously Presented) A semiconductor device, according to claim 14, wherein the island shaped hard mask is selected from the group consisting of silicon oxide.

19. (Previously Presented) A semiconductor device, according to claim 15, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

20. (Previously Presented) A semiconductor device, according to claim 15, wherein the island shaped hard mask is selected from the group consisting of silicon oxide.

w633697.1

Docket No. 740756-2653
Application No. 10/688,969
Page 4

21. (Previously Presented) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film;
an island shaped hard mask formed over the gate electrode; and
a conductive film which is in contact with the gate electrode,
wherein the conductive film is to serve as a wire for sending a signal to the gate
electrode or as a connection layer for connecting a wire with the gate electrode, and
wherein side walls of the island shaped hard mask have an angle of inclination of 0°
or more, and of 90° or less.

22. (Previously Presented) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film;
an island shaped hard mask formed over the gate electrode; and
a conductive film which is in contact with the gate electrode,
wherein the conductive film is to serve as a wire for sending a signal to the gate
electrode or as a connection layer for connecting a wire with the gate electrode, and
wherein side walls of the island shaped hard mask forms arc shapes.

23. (Previously Presented) A semiconductor device, according to claim 21, wherein
the angle is inclination of 35° or more, and 50° or less.

24. (Previously Presented) A semiconductor device, according to claim 21, wherein
the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

25. (Previously Presented) A semiconductor device, according to claim 21, wherein
the island shaped hard mask is selected from the group consisting of silicon oxide.

26. (Previously Presented) A semiconductor device, according to claim 22, wherein
the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

w633697.1

Docket No. 740756-2653
Application No. 10/688,969
Page 5

27. (Previously Presented) A semiconductor device, according to claim 22 wherein the island shaped hard mask is selected from the group consisting of silicon oxide.

W633697.1

**This Page is Inserted by IFW Indexing and Scanning
Operations and is not part of the Official Record**

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images include but are not limited to the items checked:

- ☐ **BLACK BORDERS**
- ☐ **IMAGE CUT OFF AT TOP, BOTTOM OR SIDES**
- ☐ **FADED TEXT OR DRAWING**
- ☐ **BLURRED OR ILLEGIBLE TEXT OR DRAWING**
- ☐ **SKEWED/SLANTED IMAGES**
- ☐ **COLOR OR BLACK AND WHITE PHOTOGRAPHS**
- ☐ **GRAY SCALE DOCUMENTS**
- ☒ **LINES OR MARKS ON ORIGINAL DOCUMENT**
- ☐ **REFERENCE(S) OR EXHIBIT(S) SUBMITTED ARE POOR QUALITY**
- ☐ **OTHER:** _____

IMAGES ARE BEST AVAILABLE COPY.

As rescanning these documents will not correct the image problems checked, please do not report these problems to the IFW Image Problem Mailbox.